

Substitute for Form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)

**Complete if Known**

Application Number	10/750,061
Filing Date	December 30, 2003
First Named Inventor:	Justin K. Brask, et al.
Art Unit	2812
Examiner Name	Lindsay Jr., Walter Lee
Attorney Docket No.:	42P16680

Sheet 1

of

3

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
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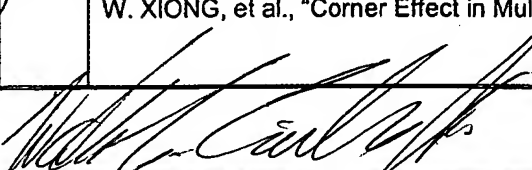
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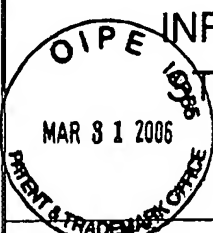
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Sheet 2	of 3	Attorney Docket No.:	42P16680	

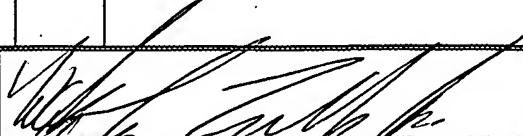
FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
WLL		WO 2004/059726 A1	07-15-2004	IBM Corporation		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
WLL		International Search Report PCT/US2005/033439, mailed 1/31/2006 (7 pgs.)	
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WLL		FU-LIANG YANG, et al., "5nm-Gate Nanowire FinFET" 2004 Symposium on VLSI Technology Digest of Technical Papers, 2004 IEEE, pgs. 196-197	
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			4/12/06

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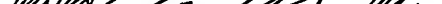
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WLL		JING GUO, et al. "Performance Projections for Ballistic Carbon Nanotube Field-Effect Transistors", Applied Physics Letters, Vol. 80, No. 17, pp. 3192-3194 (April 29, 2004)			
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